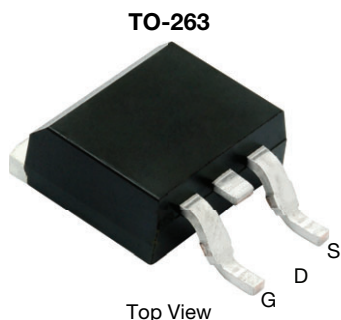
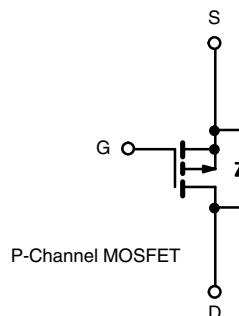


P-Channel 60 V (D-S) 175 °C MOSFET



FEATURES

- TrenchFET® power MOSFET
- Package with low thermal resistance
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


RoHS
COMPLIANT


PRODUCT SUMMARY

V_{DS} (V)	-60
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -10$ V	0.0069
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -4.5$ V	0.0088
Q_g typ. (nC)	230
I_D (A) ^d	-110
Configuration	Single

ORDERING INFORMATION

Package	TO-263
Lead (Pb)-free	SUM110P06-07L-E3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V_{DS}	-60	V
Gate-source voltage	V_{GS}	± 20	
Continuous drain current ^d ($T_J = 175$ °C)	I_D	-110	A
		-95	
Pulsed drain current	I_{DM}	-240	
Avalanche current	I_{AS}	-75	mJ
Single pulse avalanche energy ^a	E_{AS}	281	
Power dissipation	P_D	375	W
		3.75	
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYPICAL	UNIT
Junction-to-ambient	R_{thJA}	40	°C/W
Junction-to-case	R_{thJC}	0.4	

Notes

- Duty cycle ≤ 1 %
- When mounted on 1" square PCB (FR4 material)
- See SOA curve for voltage derating
- Limited by package



SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0 V, I _D = -250 μA	-60	-	-	V
Gate threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250 μA	-1	-	-3	
Gate-body leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V	-	-	± 100	nA
Zero gate voltage drain current	I _{DSS}	V _{DS} = -60 V, V _{GS} = 0 V	-	-	-1	μA
		V _{DS} = -60 V, V _{GS} = 0 V, T _J = 125 °C	-	-	-50	
		V _{DS} = -60 V, V _{GS} = 0 V, T _J = 175 °C	-	-	-250	
On-state drain current ^a	I _{D(on)}	V _{DS} = -5 V, V _{GS} = -10 V	-120	-	-	A
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = -10 V, I _D = -30 A	-	0.0055	0.0069	Ω
		V _{GS} = -10 V, I _D = -30 A, T _J = 125 °C	-	-	0.0115	
		V _{GS} = -10 V, I _D = -30 A, T _J = 175 °C	-	-	0.0138	
		V _{GS} = -4.5 V, I _D = -20 A	-	0.0070	0.0088	
Forward transconductance ^a	g _{fs}	V _{DS} = -15 V, I _D = -50 A	20	-	-	S
Dynamic ^b						
Input capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = -25 V, f = 1 MHz	-	11 400	-	pF
Output capacitance	C _{oss}		-	1200	-	
Reverse transfer capacitance	C _{rss}		-	900	-	
Total gate charge ^c	Q _g	V _{DS} = -30 V, V _{GS} = -10 V, I _D = -110 A	-	230	345	nC
Gate-source charge ^c	Q _{gs}		-	50	-	
Gate-drain charge ^c	Q _{gd}		-	60	-	
Gate resistance	R _g	f = 1 MHz	-	3	-	Ω
Turn-on delay time ^c	t _{d(on)}	V _{DD} = -30 V, R _L = 0.27 Ω I _D ≅ -110 A, V _{GEN} = -10 V, R _g = 1 Ω	-	20	30	ns
Rise time ^c	t _r		-	53	85	
Turn-off delay time ^c	t _{d(off)}		-	110	200	
Fall time ^c	t _f		-	220	430	
Drain-Source Body Diode Characteristics (T _C = 25 °C ^b)						
Continuous current	I _S		-	-	-110	A
Pulsed current	I _{SM}		-	-	-240	
Forward voltage ^a	V _{SD}	I _F = -85 A, V _{GS} = 0 V	-	-1	-1.5	V
Reverse recovery time	t _{rr}	I _F = -85 A, dI/dt = 100 A/μs	-	91	137	ns
Peak reverse recovery charge	I _{RM(REC)}		-	-6	-9	A
Reverse recovery charge	Q _{rr}		-	0.21	0.44	μC

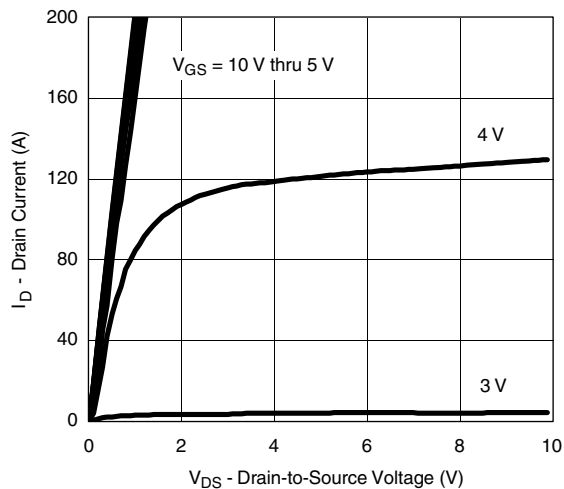
Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
b. Guaranteed by design, not subject to production testing
c. Independent of operating temperature

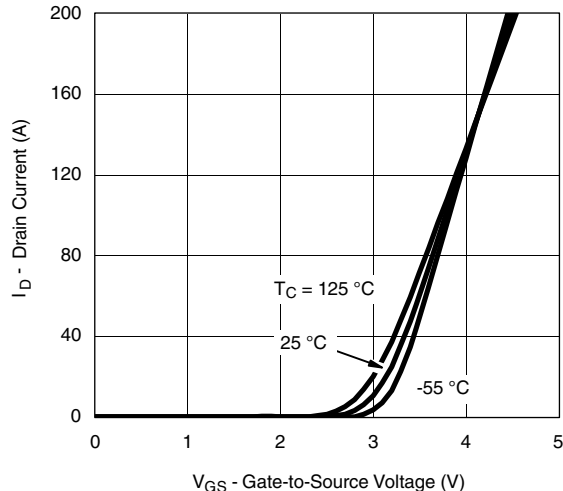
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



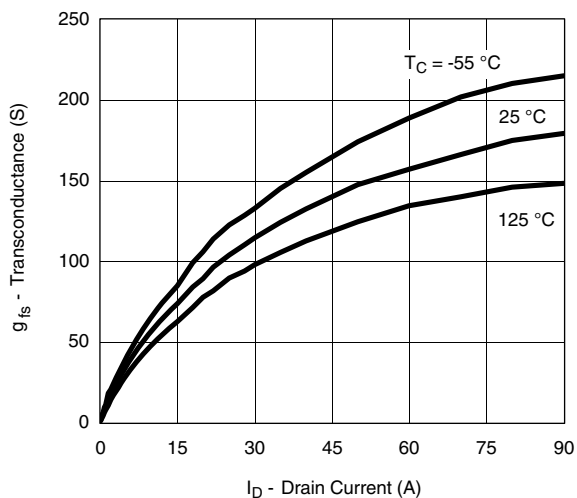
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



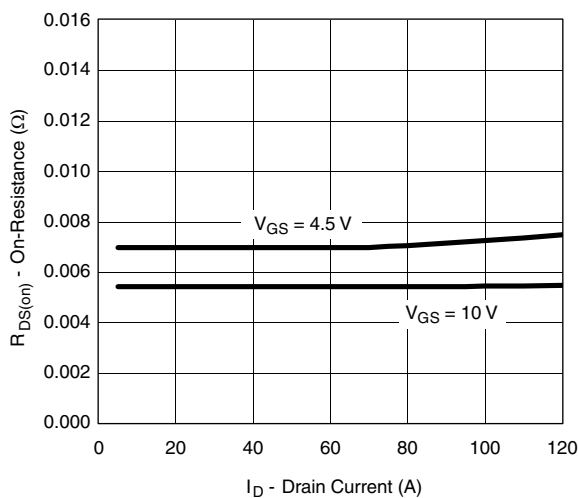
Output Characteristics



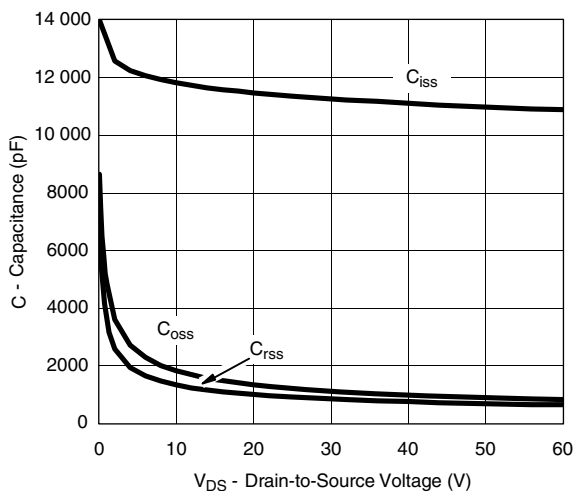
Transfer Characteristics



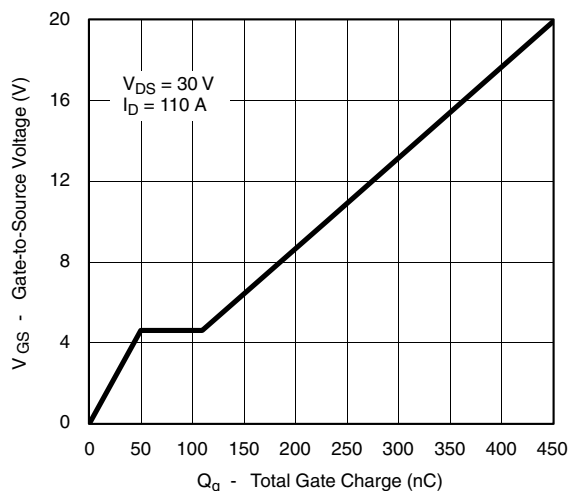
Transconductance



On-Resistance vs. Drain Current



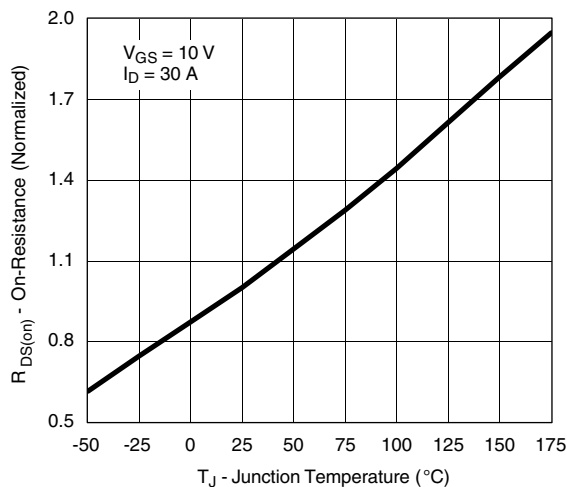
Capacitance



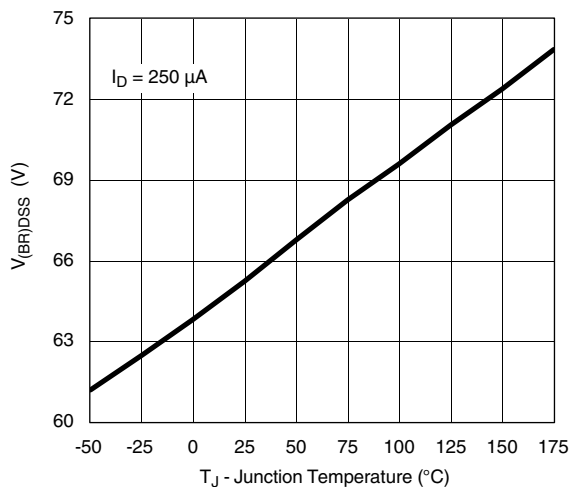
Gate Charge



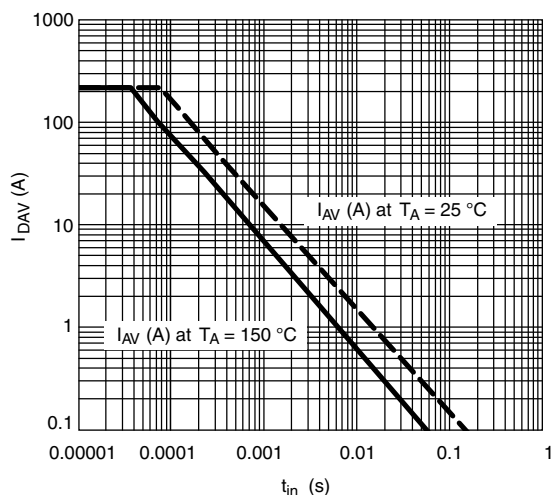
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



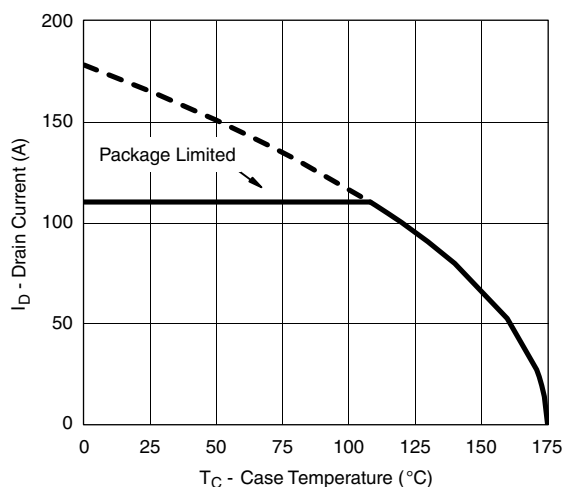
On-Resistance vs. Junction Temperature



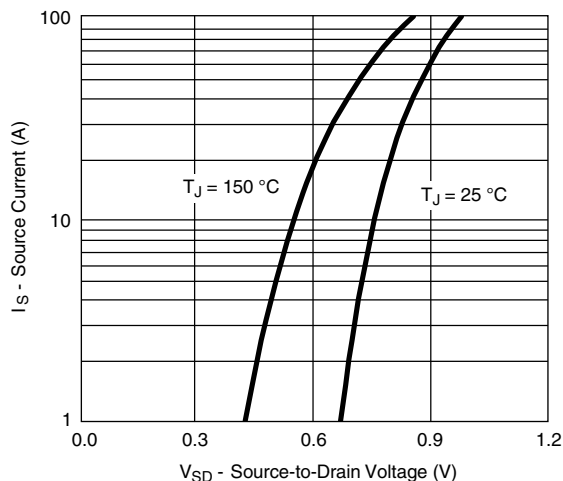
Drain Source Breakdown vs. Junction Temperature



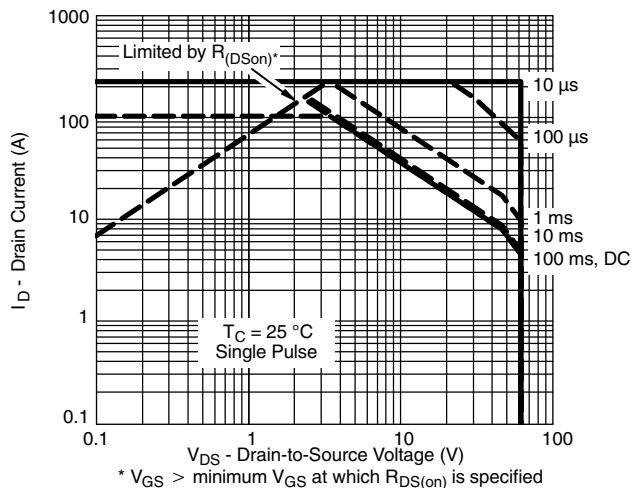
Avalanche Current vs. Time



Maximum Avalanche and Drain Current vs. Case Temperature



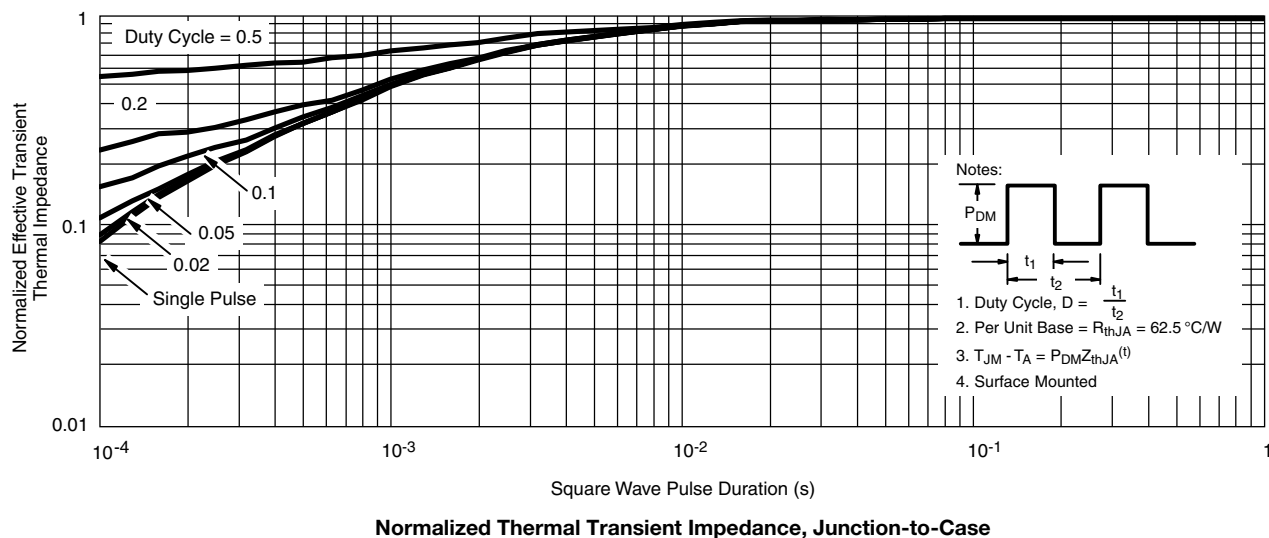
Source-Drain Diode Forward Voltage



Safe Operating Area



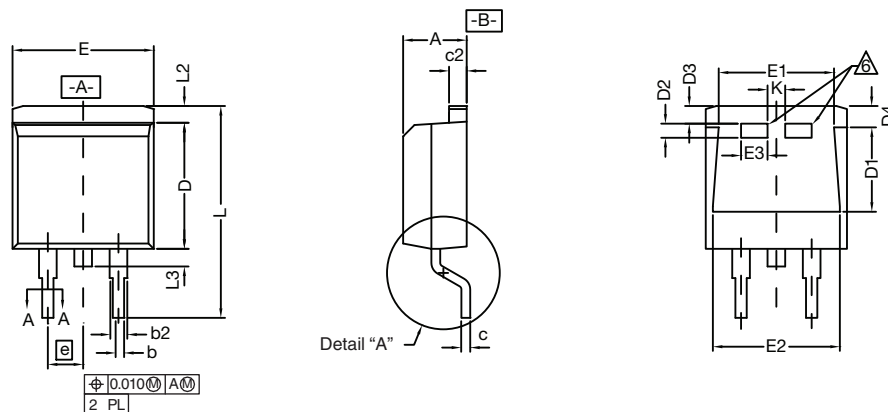
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?72439.

TO-263 (D²PAK): 3-LEAD

VERSION 1: FACILITY CODE = T



DIM.		INCHES		MILLIMETERS	
		MIN.	MAX.	MIN.	MAX.
A		0.160	0.190	4.064	4.826
b		0.020	0.039	0.508	0.990
b1		0.020	0.035	0.508	0.889
b2		0.045	0.055	1.143	1.397
c*	Thin lead	0.013	0.018	0.330	0.457
	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
	Thick lead	0.023	0.027	0.584	0.685
c2		0.045	0.055	1.143	1.397
D		0.340	0.380	8.636	9.652
D1		0.220	0.240	5.588	6.096
D2		0.038	0.042	0.965	1.067
D3		0.045	0.055	1.143	1.397
D4		0.044	0.052	1.118	1.321
E		0.380	0.410	9.652	10.414
E1		0.245	-	6.223	-
E2		0.355	0.375	9.017	9.525
E3		0.072	0.078	1.829	1.981
e		0.100 BSC		2.54 BSC	
K		0.045	0.055	1.143	1.397
L		0.575	0.625	14.605	15.875
L1		0.090	0.110	2.286	2.794
L2		0.040	0.055	1.016	1.397
L3		0.050	0.070	1.270	1.778
L4		0.010 BSC		0.254 BSC	
M		-	0.002	-	0.050

Notes

- Plane B includes maximum features of heat sink tab and plastic.
- No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- Pin-to-pin coplanarity max. 4 mils.
- *: Thin lead is for SUB, SYB.
Thick lead is for SUM, SYM, SQM.
- Use inches as the primary measurement.
-  This feature is for thick lead.



VERSION 2: FACILITY CODE = N



DIM.	MIN.	MAX.
A	4.36	4.56
A1	0	0.25
b	0.70	0.90
b1	0.51	0.89
b2	1.20	1.46
b3	1.17	1.37
c	0.38	0.694
c1	0.38	0.534
c2	1.19	1.34
D	8.60	9.00
D1	6.9	7.5
E	10.15	10.55
E1	8.1	8.7
e	2.54 BSC	
H	15.0	15.6
L	1.9	2.5
L1	-	1.65
L2	-	1.78
L3	0.25 typ.	
L4	4.78	5.28
J1	2.56	2.96
ECN: S24-1080-Rev. L, 28-Oct-2024		
DWG: 5843		

RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

[Return to Index](#)



Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Vishay products are not designed for use in life-saving or life-sustaining applications or any application in which the failure of the Vishay product could result in personal injury or death unless specifically qualified in writing by Vishay. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.